



YJD05C90HJ

N-Channel Enhancement Mode Field Effect Transisreltr



YJD05C90HJ

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D$	900	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=900V, V_{GS}=0V$	-	-	1	
		$V_{DS}=900V, V_{GS}=0V, T_J=150$	-	-	100	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}= \pm 30V, V_{DS}=0V$	-	-	± 100	nA



■ Typical Electrical and Thermal Characteristics Diagrams

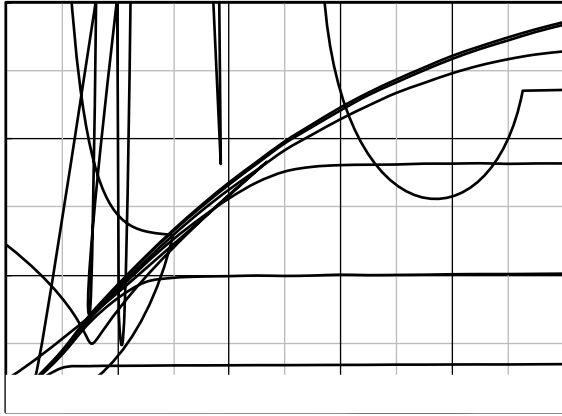


Figure 1. Output Characteristics

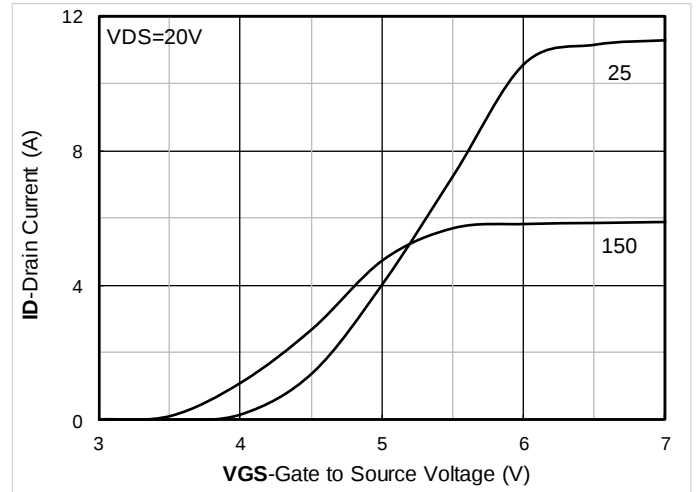


Figure 2. Transfer Characteristics

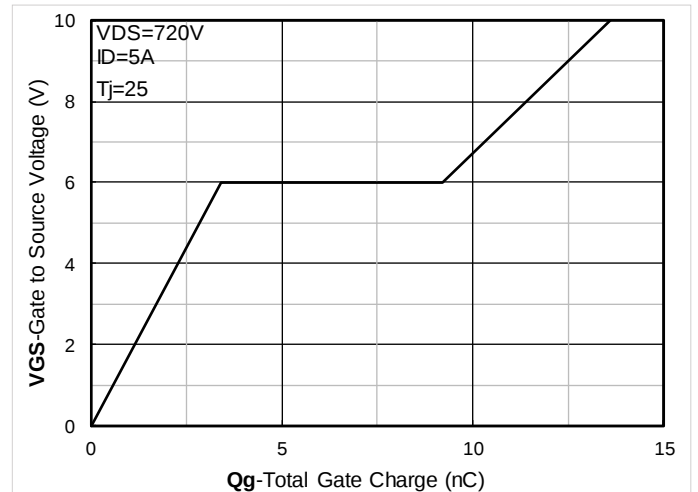


Figure 3. Capacitance Characteristics

Figure 4. Gate Charge

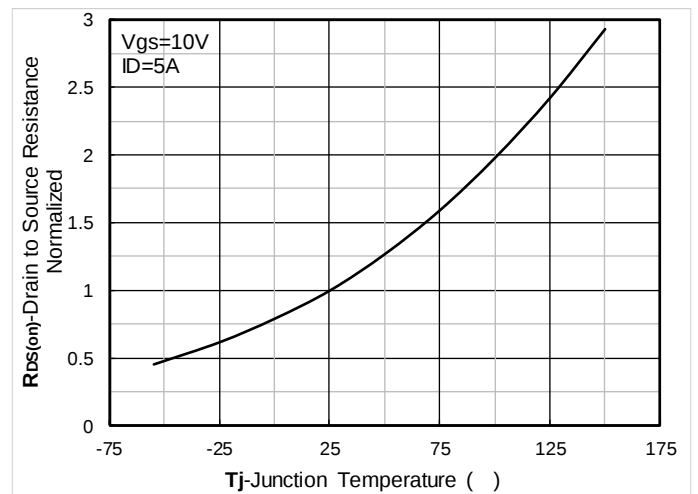


Figure 5. On-Resistance vs Gate to Source Voltage

Figure 6. Normalized On-Resistance

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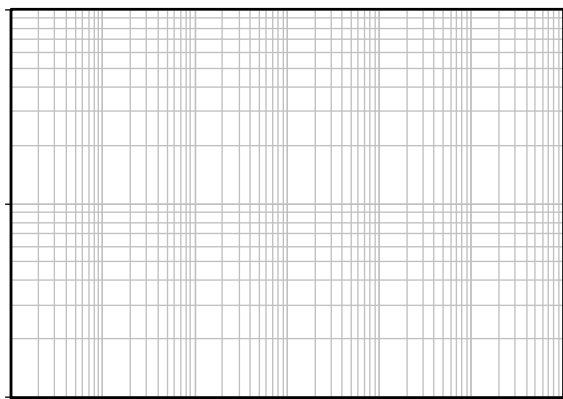


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

Test Circuits & Waveforms

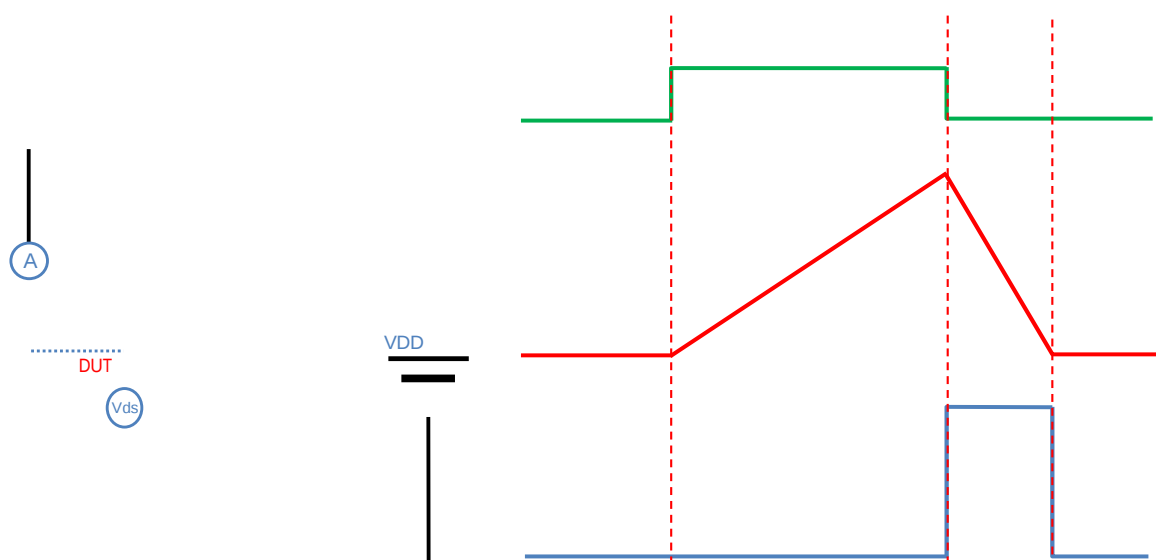


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

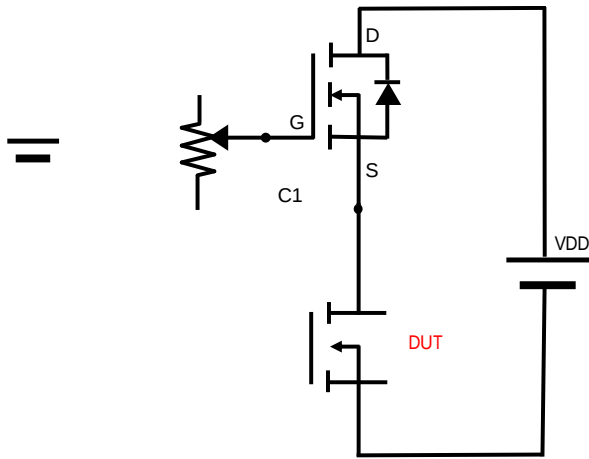


Figure B. Gate Charge Test Circuit & Waveform

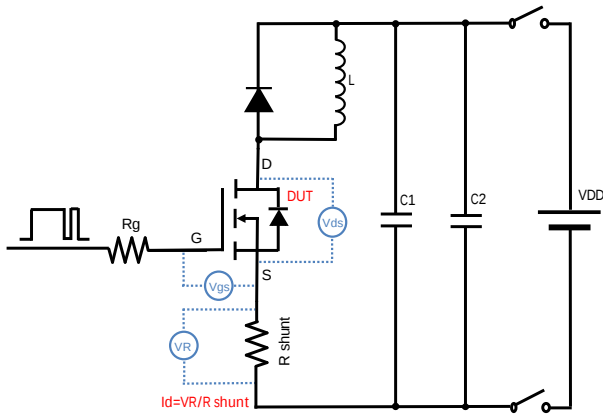


Figure C. Resistive Switching Test Circuit & Waveform

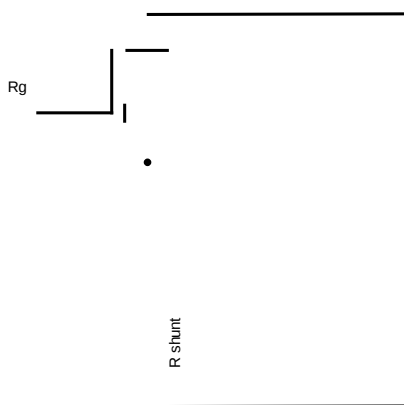


Figure D. Diode Recovery Test Circuit & Waveform



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